

Replaces January 2000 version, DS4247-4.0

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- DC Motor Control
- Welding
- Battery Chargers

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{DRM} V	Conditions
DCR1594SW28	2800	T _{.vi} = 0° to 125°C,
DCR1594SW27	2700	$I_{\text{DRM}}^{\text{v}} = I_{\text{RRM}} = 400 \text{mA},$
DCR1594SW26	2600	V_{DRM} , V_{RRM} $t_{p} = 10 \text{ms}$,
DCR1594SW25	2500	V _{DSM} & V _{RSM} =
DCR1594SW24	2400	V _{DRM} & V _{RRM} + 100V
DCR1594SW23	2300	respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1594SW25

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.

DCR1594SW

Phase Control Thyristor

DS4247-5.0 July 2001

KEY PARAMETERS

V _{DRM}		2800V
	(max)	3875A
I _{T(AV)} I _{TSM} dV/dt *	(max)	62500A
dV/dt *		1000V/ μs
dl/dt		400Α/ μs
* 11' . 1 1	VI 16 I	

* Higher dV/dt selections available

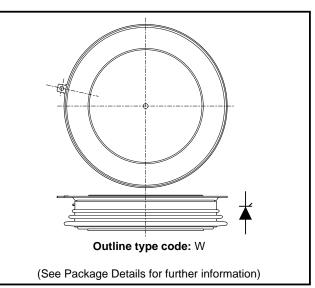


Fig. 1 Package outline

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CURRENT RATINGS

T_{case} = 60°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Max.	Units				
Double Sid	Double Side Cooled							
I _{T(AV)}	Mean on-state current	Half wave resistive load	3875	А				
I _{T(RMS)}	RMS value	-	6087	А				
Ι _τ	Continuous (direct) on-state current	-	5439	А				
Single Side	Single Side Cooled							
I _{T(AV)}	Mean on-state current	Half wave resistive load	2478	А				
I _{T(RMS)}	RMS value	-	3892	А				
Ι _τ	Continuous (direct) on-state current	-	3199	А				

T_{case} = 80°C unless stated otherwise.

Symbol	Parameter Test Conditions		Max.	Units				
Double Sid	Double Side Cooled							
I _{T(AV)}	Mean on-state current	Half wave resistive load	3035	А				
I _{T(RMS)}	RMS value	-	4765	Α				
Ι _τ	Continuous (direct) on-state current	-	4125	Α				
Single Side	Single Side Cooled							
I _{T(AV)}	Mean on-state current	Half wave resistive load	1890	А				
I _{T(RMS)}	RMS value	-	2970	A				
I_{τ}	Continuous (direct) on-state current	-	2405	А				



SURGE RATINGS

Symbol	Parameter Test Conditions		Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	50	kA
l²t	I ² t for fusing	$V_{R} = 50\% V_{RRM} - 1/4 \text{ sine}$	12.5 x 10 ⁶	A²s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	62.5	kA
l²t	I ² t for fusing	$V_R = 0$	19.5 x 10 ⁶	A²s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance - junction to case	Double side cooled	DC	-	0.008	°CW
		Single side cooled	Anode DC	-	0.016	°CW
			Cathode DC	-	0.016	°CW
R _{th(c-h)}	Thermal resistance - case to heatsink	Clamping force 70.0kN	Double side	-	0.001	°CW
		(with mounting compound)	Single side	-	0.002	°CW
T _{vj}	Virtual junction temperature	On-state (conducting)		-	135	°C
		Reverse (blocking)		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
F _m	Clamping force			63.0	77.0	kN



SURGE RATINGS

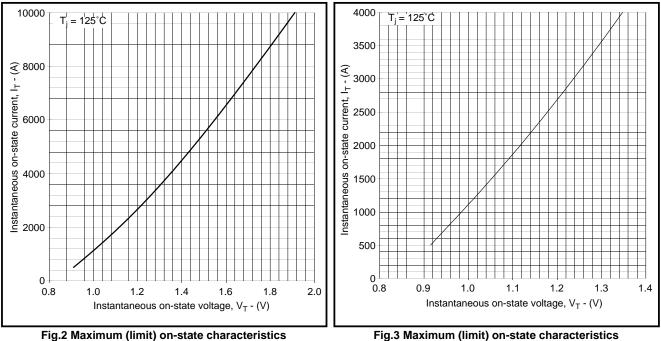
Symbol	Parameter	Test Conditions		Min.	Max.	Units
I _{RRM} /I _{RRM}	Peak reverse and off-state current	At $V_{\text{RRM}}/V_{\text{DRM}}$, $T_{\text{case}} = 125^{\circ}\text{C}$		-	400	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C	To 67% V_{DRM} , $T_j = 125$ °C, Gate open		1000	V/µs
dl/dt	Rate of rise of on-state current	From 67% V_{DRM} to 2x $I_{T(AV)}$	Repetitive 50Hz	-	250	A/μs
		Gate source 30V, 10Ω,	Non-repetitive	-	400	A/μs
		$t_r \le 0.5 \mu s$, $T_j = 125^{\circ} C$				
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C		-	0.94	V
r _T	On-state slope resistance	At T _{vj} = 125°C		-	0.099	mΩ
t _{gd}	Delay time	$V_{\rm D}$ = 67% $V_{\rm DRM}$, gate source 30V, 15 Ω		0.5	2.0	μs
		t _r = 0.5μs, Tj = 25°C				
t _q	Turn-off time	$I_{T} = 5000A, t_{p} = 3.5ms, T_{j} = 125^{\circ}C,$		450	900	μs
		$V_{R} = 900V, dI_{RR}/dt = 4A/\mu s,$				
		V _{DR} = 67% V _{DRM} ,				
		$dV_{DR}/dt = 20V/\mu s$ linear				
Ι _L	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		100	1000	mA
I _H	Holding current	$T_{j} = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500A, I_{T} = 5A$		50	250	mA



GATE TRIGGER CHARACTERISTICS AND RATINGS

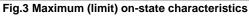
Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	$V_{\text{DRM}} = 5V, T_{\text{case}} = 25^{\circ}\text{C}$	4	V
I _{GT}	Gate trigger current	$V_{\text{DRM}} = 5V, T_{\text{case}} = 25^{\circ}\text{C}$	400	mA
V _{GD}	Gate non-trigger voltage	At V _{DRM} T _{case} = 125°C	0.25	V
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	V
V _{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	V
V _{RGM}	Peak reverse gate voltage	-	5	V
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode	30	А
Р _{бм}	Peak gate power	See table fig. 8 and 9	150	w
P _{G(AV)}	Mean gate power	-	10	W

CURVES



V_{TM} EQUATION

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$



Where A = 1.152158 B = -0.08401428 $C = 3.351054 \times 10^{-5}$ D = 0.01199439these values are valid for $T_i = 125^{\circ}C$ for $I_T 500A$ to 10000A

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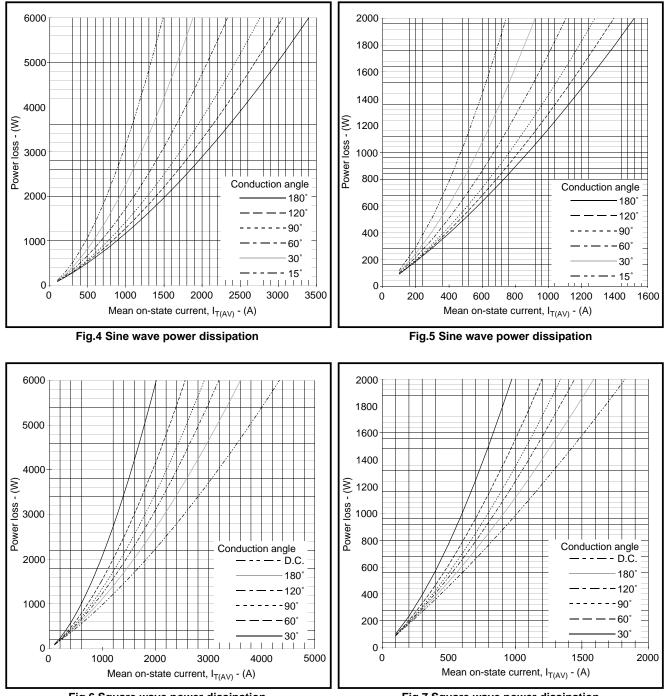
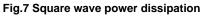


Fig.6 Square wave power dissipation





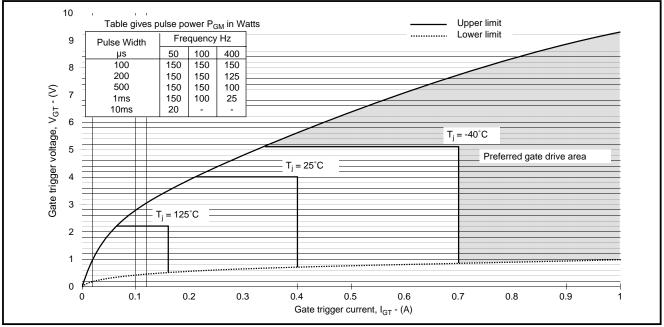


Fig.8 Gate characteristics

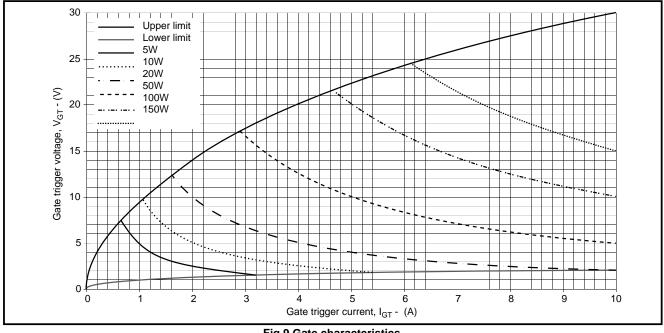
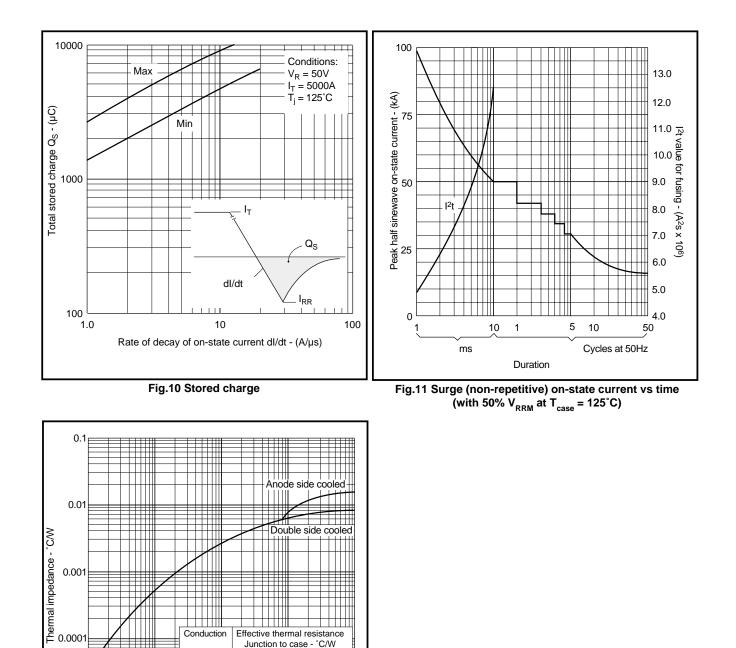


Fig.9 Gate characteristics





Single sided

0.0160

0.0168

0.0170

0.0180

10

Effective thermal resistance Junction to case - °C/W

1.0

Double sided

0.0080

0.0088

0.0090

0.0100

Conduction

d.c. half wave

3 phase 120°

6 phase 60°

0.1

Time - (s)

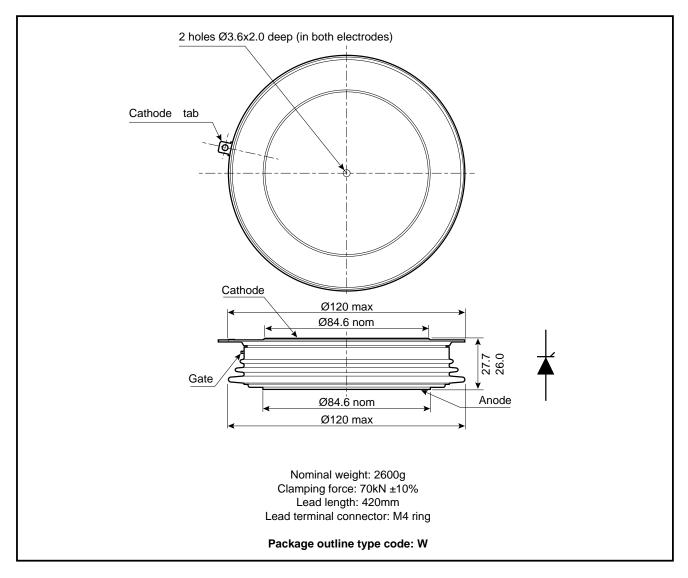
0.01

0.00001



PACKAGE DETAILS

For further package information, please visit our website or contact your nearest Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACS range includes a varied selection of pre-loaded clamps to suit all of our manufactured devices. Types available include cube clamps for single side cooling of 'T' 23mm and 'E' 30mm discs, and bar clamps right up to 83kN for our 'Z' 100mm thyristors and diodes.

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or customer service office.



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Dynex Semiconductor annotate datasheets in the top right hard corner of the front page, to indicate product status. The annotations are as follows:-

Target Information: This is the most tentative form of information and represents a very preliminary specification. No actual design work on the product has been started.

Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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